

JAW EC-400 (Woolam Spectroscopic)																	Brian Lingg, PM						
Date	User	Film	Recipe	Substrate T	Thickness	Dep.time	Water center	Index @ 632.8nm	Index @ 1550nm	Dep.rate	Stress	HF etch rate wafer	AVG dep.rate	AVG+10%	AVG-10%	AVG index@	AVG+2%	AVG-2%	AVG.Stress	AVG+10%	AVG-10%	Additional Notes	
1/1/2012	User	SIN	SIN_10	250 °C	(A)	sec				(nm/min)	Mpa	(nm/min)											Deposition done on 4" Si wafer
01/06/14	Bijjana	SIN	SIN_10	250	1055.25	568.1	1.949	1.899	11.15	571.87			11.21	12.33	10.09	1.959	1.998	1.920	508.86	610.63	407.09		
01/23/14	Bijjana	SIN	SIN_10	250	1133.40	568.1	1.935	1.890	11.97	446.88	90.66		11.21	12.33	10.09	1.959	1.998	1.920	508.86	610.63	407.09		1/23/14
02/03/14	Bijjana	SIN	SIN_10	250	1046.60	568.1	1.937	1.893	11.05	486.75	81.21		11.21	12.33	10.09	1.959	1.998	1.920	508.86	610.63	407.09		
02/19/14	Bijjana	SIN	SIN_10	250	1030.66	568.1	1.935	1.890	10.89	353.92	77.32		11.21	12.33	10.09	1.959	1.998	1.920	508.86	610.63	407.09		2/14/14 Silane change
03/14/14	Bijjana	SIN	SIN_10	250	1042.16	568.1	1.933	1.887	11.01	684.87	92.89		11.21	12.33	10.09	1.959	1.998	1.920	508.86	610.63	407.09		

Avg.Thickness	1061.614
Avg. Index	1.938
Avg+2%	1.977
Avg-2%	1.899
Avg Dep. Rate	11.21
Avg +10%	12.33
Avg -10%	10.09
Avg. Stress	508.86
Avg +20%	610.63
Avg -20%	407.09
Avg. HF e.r.	85.52

